

EYP-DFB-0763-00030-1500-SOT02-0000



We focus on power.

Version 0.90

2009-10-22

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DISTRIBUTED FEEDBACK LASER

GaAs Semiconductor Laser Diode
with integrated grating structure



General Product Information

Product	Application
763 nm DFB Laser with TO Housing	Spectroscopy
Monitor Diode	O ₂ Detection
	Metrology



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T _S	°C	-40		85
Operational Temperature at Case	T _C	°C	10		40
Forward Current	I _F	mA			130
Reverse Voltage	V _R	V			0
Output Power	P _{opt}	mW			35

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	15		35
Operational Temperature at Laser Chip	T _{LD}	°C	15		35
Forward Current	I _F	mA			120
Output Power	P _{opt}	mW	5		30

Measurement Conditions / Comments

total output measured with integrating sphere

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ _C	nm	762	763	764
Spectral Width (FWHM)	Δv	MHz		2	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dI	nm / mA		0.003	
Output Power @ I _F = 120 mA	P _{opt}	mW	30		

Measurement Conditions / Comments

see images on page 4

total output measured with integrating sphere

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RWE/RWL



BAL



DFB/DBR



TPL/TPA

Characteristics at T_{amb} 25 °C at Begin Of Life cont'd

Parameter	Symbol	Unit	min	typ	max
Slope Efficiency	S	W / A	0.4		0.7
Threshold Current	I_{th}	mA			70
Divergence parallel (FWHM)	$\Theta_{ }$	°		8	
Divergence perpendicular (FWHM)	Θ_{\perp}	°		21	
Sidemode Suppression Ratio	SMSR	dB	30	45	
Polarization Extinction Ratio	PER	dB		20	
Spatial Mode (transversal)				TEM ₀₀	

Measurement Conditions / Comments

perpendicular to Pin 2 - Pin 3 - plane

parallel to Pin 2 - Pin 3 - plane

 $P_{opt} = 30$ mW $P_{opt} = 30$ mW; E field perpendicular to Pin 2 - 3 - plane
fundamental mode**Monitor Diode**

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I_{mon} / P_{opt}	$\mu A / mW$	0.5		10
Reverse Voltage Monitor Diode	U_{RMD}	V	3		5

Measurement Conditions / Comments $U_R = 5$ V, target values

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Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	l_{PIN}	mm		14	

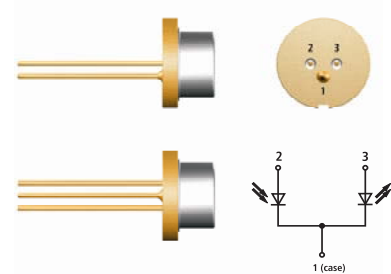
Measurement Conditions / Comments

reference plane: top side of TO header

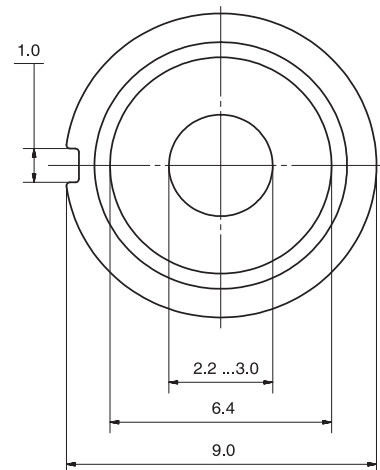
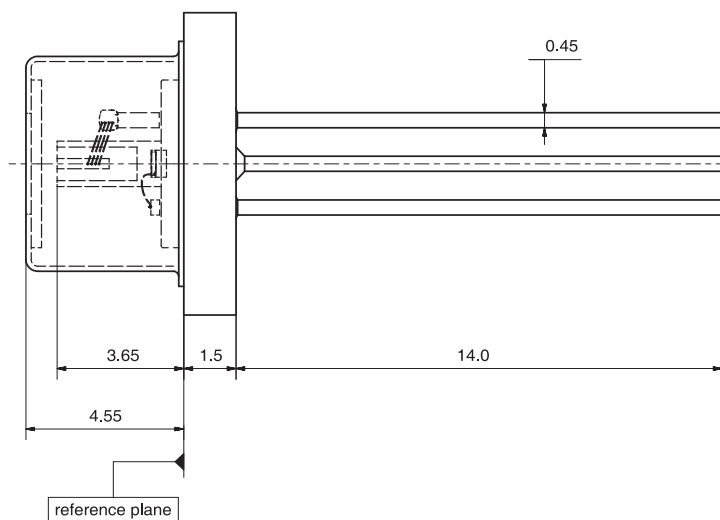
reference: center of outer diameter of header

Package Pinout

Ground	1
Photo Diode (+)	2
Laser (+)	3



Package Drawings



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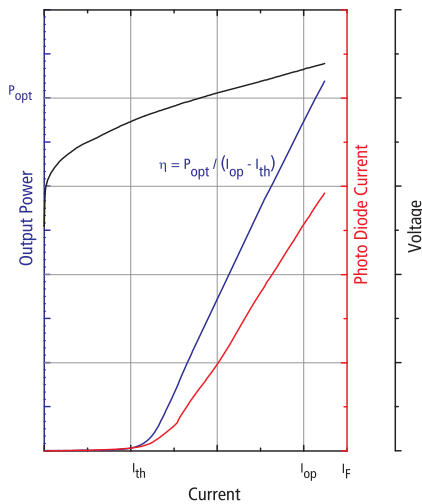
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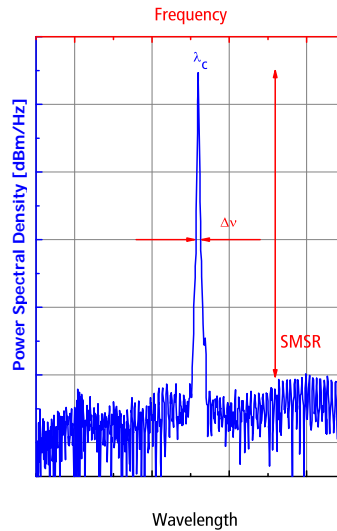


Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

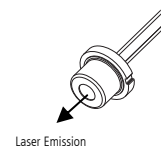
Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The DFB diode type is known to be sensitive against optical feedback, so an optical isolator may be required in some cases. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



Laser Emission



IEC 60825-1



Complies with 21 CFR 1040.10 and 1040.40

